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- Incident energy ··· 100eV~ 300eV Time interval of injections ·· 1000fs(simulation) After each incidence, the system is cooled and brought to thermal equilibrium at a given temperature. Substrate temperature ··· 300K Motion of atoms is calculated by the molecular dynamics (MD) simulation.
- Stillinger-Weber potential is used for MD simulations.













Conclusions and discussion

- Si sputtering yields by atomic O injections are obtained as functions of injection dose for different incident energies.
- The Si sputtering yield by atomic O injections at steady state is obtained as a function of incident energy
- Dose dependence of sputtering yields at small dose needs to be examined further.